

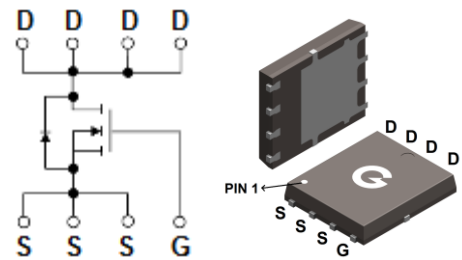
Features

- High speed power switching
- Enhanced body diode dv/dt capability
- Enhanced avalanche ruggedness
- RoHS compliant with Halogen-free

HF

Mechanical Data

- Case: PDFN5×6-8L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



PDFN5×6-8L

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL200N15TH-5DL8	PDFN5×6-8L	5000 pcs / Tape & Reel	200N15TH

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	150	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _C = 25°C)	I _D	50	A
Continuous Drain Current (T _C = 100°C)	I _D	32	A
Pulsed Drain Current	I _{DM}	200	A
Single Pulse Avalanche Energy *3	E _{AS}	80	mJ

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (T _C = 25°C)	P _D	113	W
Thermal Resistance Junction-to-Air *1	R _{θJA}	50	°C/W
Thermal Resistance Junction-to-Case	R _{θJC}	1.1	°C/W
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	150	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 150V, V _{GS} = 0V, T _J = 25°C	-	-	1	μA
		V _{DS} = 150V, V _{GS} = 0V, T _J = 100°C	-	-	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *2	V _{GS} = 10V, I _D = 20A	-	-	20	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	3	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	1960	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 75V	-	130	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1.0MHz	-	8	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *4	V _{DD} = 75V	-	9	-	ns
t _r	Turn-on Rise Time *4	V _{GS} = 10V	-	8	-	
t _{d(OFF)}	Turn-Off Delay Time *4	R _G = 10Ω	-	15	-	
t _f	Turn-Off Fall Time *4	I _D = 20A	-	9	-	
Q _G	Total Gate-Charge	V _{DD} = 75V	-	25	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = 10V	-	9	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 20A	-	3	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _{SD} = 20A, V _{GS} = 0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} = 20A, V _{GS} = 0V	-	60	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt = 100A/μs	-	120	-	nC

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH$
- Guaranteed by design, not subject to production testing

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

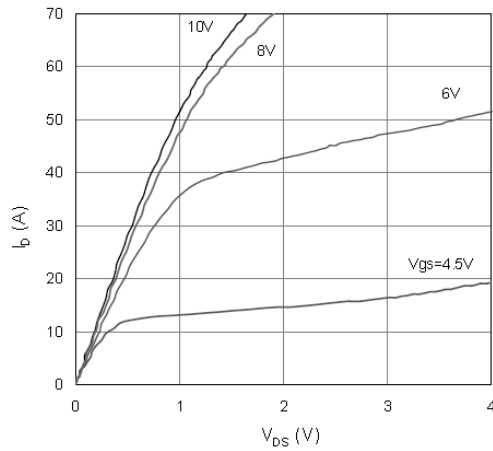


Fig 1 Typical Output Characteristics

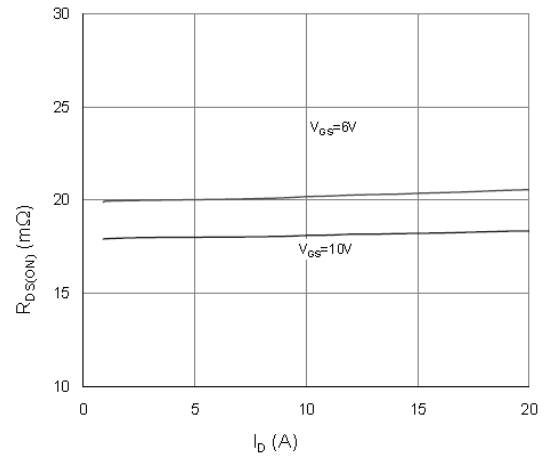


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

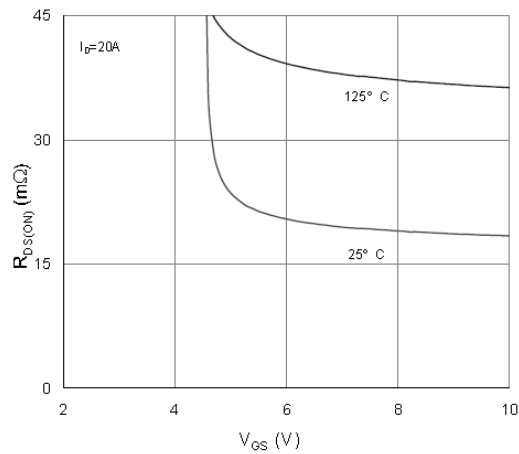


Fig 3 On-Resistance vs. Gate-Source Voltage

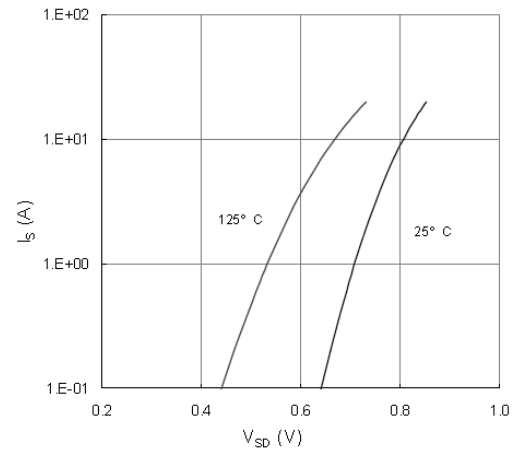


Fig 4 Body-Diode Characteristics

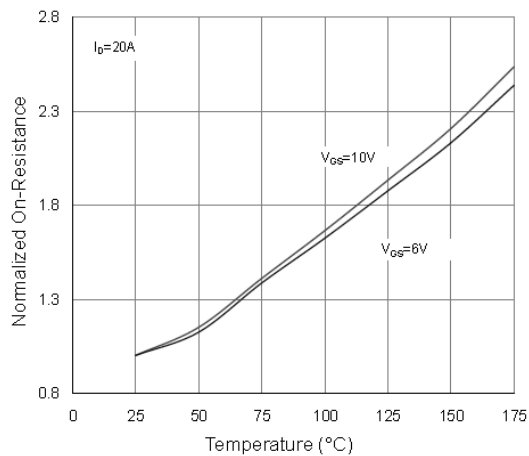


Fig 5 On-Resistance vs. Junction Temperature

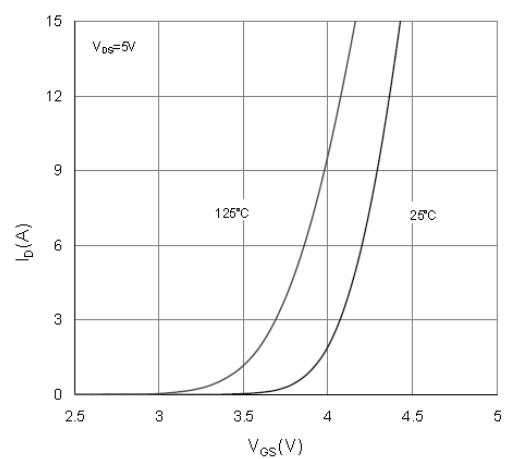


Fig 6 Transfer Characteristics

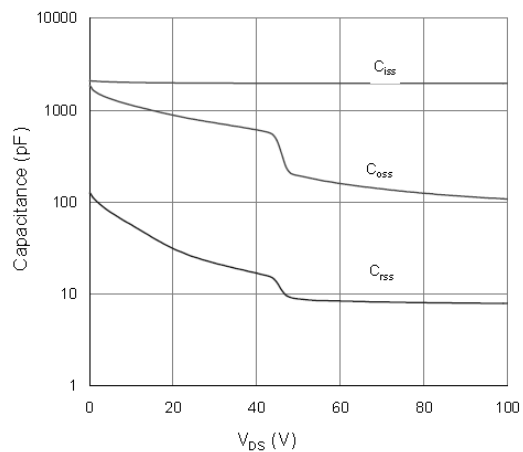


Fig 7 Capacitance Characteristics

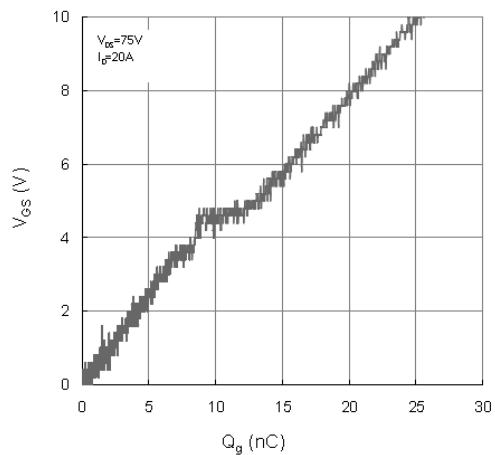


Fig 8 Gate-Charge Characteristics

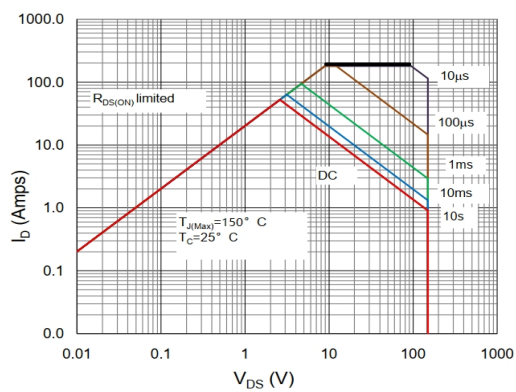
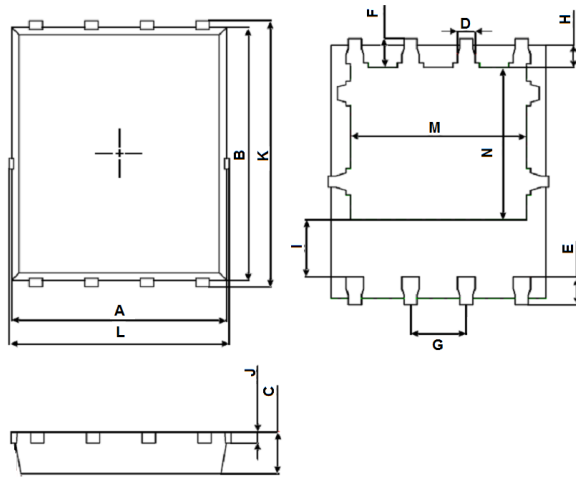


Fig 9 Safe Operating Area

Package Outline Dimensions (Unit: mm)



PDFN5x6-8L		
Dimension	Min.	Max.
A	4.824	4.976
B	5.674	5.826
C	0.900	1.000
D	0.350	0.450
E	0.559	0.711
F	0.574	0.726
G	1.250	1.290
H	0.424	0.576
I	1.190	1.390
J	0.154	0.354
K	5.974	6.126
L	4.944	5.096
M	3.910	4.110
N	3.375	3.575

Mounting Pad Layout (Unit: mm)

PDFN5x6-8L

